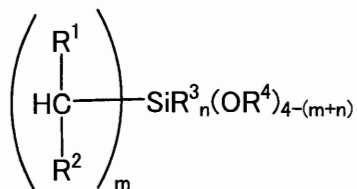


ABSTRACT

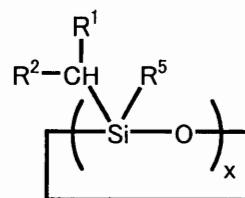
A material for insulating film suitable as an interlayer insulating material for a semiconductor device, from which an insulating film is formed by chemical vapor deposition, and an insulating film formed from such a material and a semiconductor device employing an insulating film, are provided.

A material for insulating film comprising an organosilicon compound which is one of an organosilane compound in which a secondary hydrocarbon group and an alkenyl group, or an alkenyl group, is directly bonded to a silicon atom, or an organosiloxane compound in which a secondary hydrocarbon group and/or an alkenyl group is directly bonded to a silicon atom, represented by the formulae (1) to (4), from which an insulating film is formed by chemical vapor deposition of the organosilicon compound:

(1)



(2)



20 (3)

(4)

